



PATENT ABSTRACTS OF JAPAN

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(21) Application number: **04001439**(71) Applicant: **SEIKO EPSON CORP**(22) Date of filing: **08.01.92**(72) Inventor: **MOROZUMI YUKIO****(54) SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF****(57) Abstract:**

PURPOSE: To improve reliability and yield of electric characteristics and quality and to contribute to stably supply of a semiconductor device having finer miniaturization and many functions by laminating plasma reacted NSG and PSG films using organic silane on silicide electrode wiring and an impurity layer in a MOSLSI, etc., and further forming an interlayer insulating film flattened with coating glass.

CONSTITUTION: After coating glass 22 on NSG 20 and PSG 21 films plasma reacted with TEOS on gate electrode wiring 14 Ti-silicified on its surface and an impurity layer 7 are spin coated and annealed at 800°C, a contact hole is opened by wet etching with aqueous HF solution and anisotropic reactive ion etching, and then metal wiring 23 is provided.

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